

SILICON TRANSISTOR $\mu PA800T$

HIGH-FREQUENCY LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR (WITH BUILT-IN 2 ELEMENTS) MINI MOLD

The μ PA800T has built-in 2 low-voltage transistors which are designed to amplify low noise in the VHF band to the UHF band.

FEATURES

- Low Noise
 NF = 1.9 dB TYP. @ f = 2 GHz, VcE = 1 V, Ic = 3 mA
- High Gain $|S_{21e}|^2 = 6.5 \text{ dB TYP.} @ f = 2 \text{ GHz, Vce} = 1 \text{ V, Ic} = 3 \text{ mA}$
- · A Mini Mold Package Adopted
- Built-in 2 Transistors (2 × 2SC4228)

ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKING STYLE
μΡΑ800Τ	Loose products (50 PCS)	Embossed tape 8 mm wide. Pin 6 (Q1 Base), Pin 5 (Q2 Base), Pin 4 (Q2 Emitter) face to perforation side of the tape.
μPA800T-T1	Taping products (3 KPCS/Reel)	

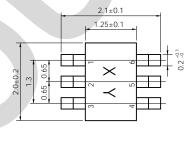
Remark To order evaluation samples, please contact your nearby sales office. Part number for sample order: $\mu PA800T$ -A (Unit Sample quantity is 50 pcs.)

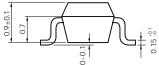
ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

PARAMETER	SYMBOL	RATING	UNIT
Collector to Base Voltage	Vcво	20	V
Collector to Emitter Voltage	VCEO	10	V
Emitter to Base Voltage	V _{EBO}	1.5	V
Collector Current	Ic	35	mA
Total Power Dissipation	Рт	150 in 1 element 200 in 2 elements ^{Note}	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65 to +150	°C

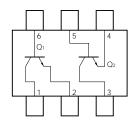
Note 110 mW must not be exceeded in 1 element.

PACKAGE DRAWINGS (Unit: mm)





PIN CONFIGURATION (Top View)



PIN CONNECTIONS
1. Collector (Q1) 4. Emitter (Q2)

1. Collector (Q1) 4. Emitter (Q 2. Emitter (Q1) 5. Base (Q2) 3. Collector (Q2) 6. Base (Q1)

The information in this document is subject to change without notice.

ELECTRICAL CHARACTERISTICS (TA = 25 °C)

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	Ісво	Vcb = 10 V, IE = 0			1.0	μΑ
Emitter Cutoff Current	ІЕВО	V _{EB} = 1 V, I _C = 0			1.0	μА
DC Current Gain	hfE	$V_{CE} = 3 \text{ V}, \text{ Ic} = 5 \text{ mA}^{\text{Note 1}}$	80		200	
Gain Bandwidth Product	f⊤	VcE = 3 V, Ic = 5 mA	5.5	80		GHz
Feed-back Capacitance	Сге	$V_{CB} = 3 \text{ V}, \text{ I}_E = 0, \text{ f} = 1 \text{ MHz}^{\text{Note 2}}$			0.7	pF
Insertion Power Gain (1)	S _{21e} ²	VcE = 1 V, Ic = 3 mA, f = 2 GHz	4.5	6.5		dB
Insertion Power Gain (2)	S _{21e} ²	VcE = 3 V, Ic = 5 mA, f = 2 GHz	5.5	7.5		dB
Noise Figure (1)	NF	VcE = 1 V, Ic = 3 mA, f = 2 GHz		1.9	3.2	dB
Noise Figure (2)	NF	Vce = 3 V, Ic = 5 mA, f = 2 GHz		1.9	3.2	dB

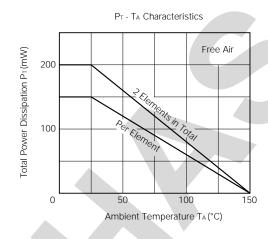
Notes 1. Pulse Measurement: Pw \leq 350 μ s, Duty cycle \leq 2 %

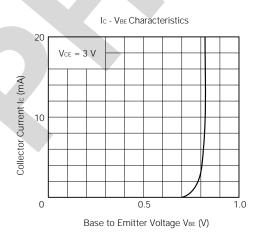
2. Measured with 3-pin bridge, emitter and case should be connected to guard pin of bridge.

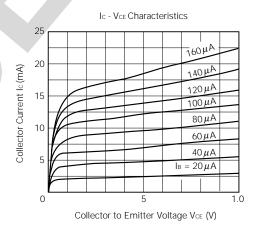
hfe CLASSIFICATION

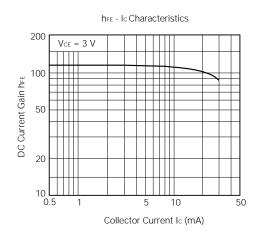
Rank	КВ			
Marking	RL			
hfe Value	80 to 200			

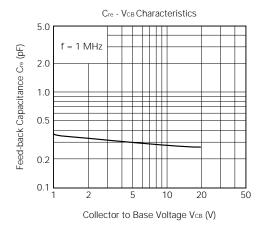
TYPICAL CHARACTERISTICS (TA = 25 °C)

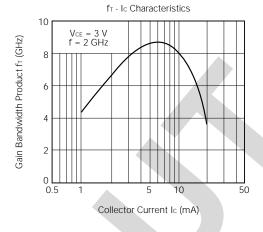


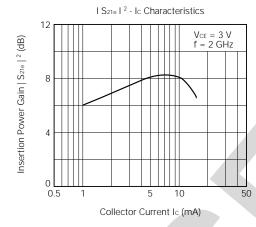


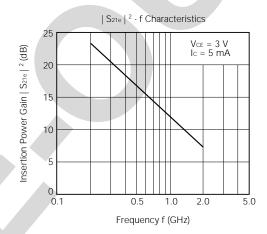


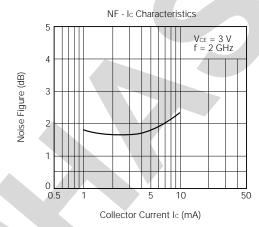












S-PARAMETERS

$V_{CE} = 3 V$, $I_{C} = 5 mA$, Z_{O}

V_{CE} = 3 V, Ic = 5 mA, Zo = 50 Ω								
FREQUENCY	S	11		S21		S12	S	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.00	.875	-18.6	14.087	161.1	.018	78.2	.958	-10.1
200.00	.762	-35.0	12.290	145.1	.034	68.6	.888	-17.7
300.00	.677	-47.2	10.888	133.6	.048	66.6	.800	-24.4
400.00	.565	-59.4	9.275	123.6	.055	65.8	.719	-26.7
500.00	.495	-67.5	8.300	115.7	.063	63.5	.669	-28.7
600.00	.425	-76.1	7.184	108.9	.074	61.1	.610	-30.3
700.00	.372	-81.6	6.454	104.8	.084	63.8	.600	-30.6
800.00	.327	-88.5	5.818	99.5	.089	62.7	.560	-31.3
900.00	.289	-93.6	5.231	95.5	.092	64.6	.543	-30.1
1000.00	.255	-100.5	4.820	92.0	.104	62.8	.519	-33.4
1100.00	.236	-105.2	4.444	88.8	.105	64.2	.512	-31.8
1200.00	.214	-112.2	4.142	85.3	.113	64.2	.497	-33.4
1300.00	.195	-117.6	3.842	83.2	.122	63.6	.476	-33.2
1400.00	.182	-123.8	3.554	79.3	.127	65.0	.481	-34.2
1500.00	.165	-129.9	3.343	77.4	.139	64.1	.467	-34.6
1600.00	.153	-124.4 -137.4	3.218	75.3	.140	64.5	.466	-34.8
1700.00	.145	-144.3	3.091	73.6	.152	65.4	.458	-37.2
1800.00	.139	-144.3 -151.8	2.857	70.4	.162	64.3	.456	-36.1
1900.00	.134	-151.6 -157.0	2.764	68.7	.162	62.3	.451	-38.4
2000.00	.129	-164.7	2.624	66.4		64.8		-39.0
2000.00	.129	-104.7	2.024	00.4	.176	04.0	.445	-39.0
Vce = 3 V, Ic = 3 I	m / 70 - F	50.0						
VCE = 3 V, IC = 3 I	IIIA, 20 = 3	22 00						
FREQUENCY	S	11	9	S21		S12	S	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.00	.943	-13.4	9.384	165.9	.020	84.1	.969	-7.7
200.00	.868	-26.6	8.668	152.8	.038	77.2	.936	-13.8
300.00	.815	-37.7	8.165	142.9	.051	67.9	.876	-20.9
400.00	.717	-48.9	7.279	132.9	.062	63.9	.804	-23.5
500.00	.655	-56.8	6.780	125.5	.075	63.9	.764	-26.7
600.00	.577	-65.5	6.061	118.0	.084	60.0	.708	-29.7
700.00	.518	-71.2	5.504	112.8	.091	59.7	.685	-31.1
800.00	.468	-78.1	5.074	106.7	.098	57.0	.639	-32.0
900.00	.420	-83.7	4.632	102.8	.102	59.0	.611	-32.8
1000.00	.380	-90.6	4.340	98.3	.105	56.6	.592	-35.0
1100.00	.344	-94.8	3.951	94.8	.112	57.8	.579	-34.1
1200.00	.321	-101.6	3.717	90.5	.121	59.0	.551	-35.0
1300.00	.291	-105.9	3.485	87.6	.128	58.7	.532	-35.9
1400.00	.273	-111.7	3.306	84.3	.135	59.8	.535	-36.6
1500.00	.250	-117.2	3.134	80.7	.140	58.0	.511	-37.5
1600.00	.228	-122.4	2.959	79.0	.145	59.5	.516	-37.7
1700.00	.219	-128.5	2.819	76.0	.153	59.0	.504	-39.0
1800.00	.199	-135.3	2.699	73.9	.161	58.4	.493	-39.9
1900.00	.193	-139.6	2.572	71.9	.163	60.3	.489	-41.4
2000.00	.182	-146.9	2.474	68.3	.175	59.8	.482	-41.4
Vce = 3 V, Ic = 1	mΔ 70 - F	50.0						
VCE - 3 V, IC - 1 1	IIIA, 2 0 – 3	30 32						
FREQUENCY	S	11		521		S12	S	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.00	1.023	-7.6	3.505	172.1	.025	86.4	.995	-4.6
200.00	.983	-7.6 -16.1	3.400	163.3	.025	79.3	.986	-4.6 -7.8
300.00	.975	-22.4	3.400	157.3	.061	74.6	.976	-7.8 -12.8
400.00	.922	-22.4 -31.8		149.1	.075	70.7	.936	-12.6 -15.1
500.00	.899	-31.6 -36.9	3.219 3.186	143.3	.073	66.4	.922	-13.1 -18.8
600.00	.849	-30.9 -44.7	3.046	135.7	.105	62.2	.885	-22.5
700.00	.812	-44.7 -50.6	2.905	131.1	.103	61.7	.880	-22.3 -24.4
800.00	.774	-57.1	2.830	124.4	.113	55.7	.846	-24.4 -27.2
900.00	.727	-62.9		119.2	.134		.808	
1000.00	.680	-62.9 -69.3	2.694 2.597	114.1	.134	55.6 53.7	.790	-28.8 -31.8
1100.00	.651	-09.3 -74.1	2.597	109.3	.146	50.3	.766	-31.8 -32.8
1200.00	.616	-74.1 -79.8	2.479	104.8	.146	49.8	.741	-34.9
1300.00	.575	-79.6 -85.2	2.392	104.6	.155	46.2	.714	-34.9 -35.9
1400.00	.575 .546	-85.2 -90.6	2.302	96.0	.160	46.2 46.7	.714	-35.9 -36.8
1500.00	.512	-90.6 -95.8	2.207	92.1	.168	43.6	.685	-38.4
1600.00	.481	-95.6 -100.6	2.110	88.8	.165	45.5	.676	-36.4 -40.1
1700.00	.463	-106.3	1.989	85.5	.176	45.3	.667	-40.1 -41.8
1800.00	.440	-100.3 -111.8	1.903	82.2	.173	43.8	.649	-41.8 -42.3
1900.00	.419	-116.4	1.854	78.9	.173	43.5	.633	-44.2
2000.00	.394	-121.2	1.779	75.5	.173	43.7	.630	-45.2
2000.00	. =	· · -		. 0.0			. 300	

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